



JX075 Series Sensitive gate SCRs

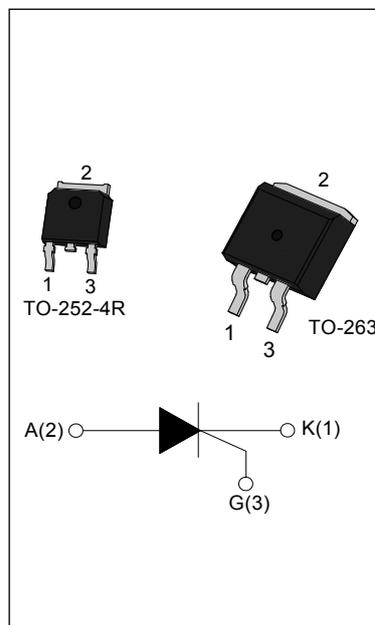
Rev.8.0

DESCRIPTION:

The JX075 SCR series provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package TO-252-4R & TO-263 are RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
V_{DSM}/V_{RSM}	1000	V
$I_{T(RMS)}$	12	A
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range		T_j	-40-125 ^①	$^{\circ}C$
Non-repetitive peak off-state voltage		V_{DSM}	1000	V
Non-repetitive peak reverse voltage		V_{RSM}	1000	V
RMS on-state current	TO-252-4R ($T_c=80^{\circ}C$)	$I_{T(RMS)}$	12	A
	TO-263 ($T_c=95^{\circ}C$)			
Non repetitive surge peak on-state current ($t_p=10ms$)		I_{TSM}	100	A
I^2t value for fusing ($t_p=10ms$)		I^2t	50	A^2s
Critical rate of rise of on-state current		di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^{\circ}C$)		I_{GM}	1.2	A
Peak gate power ($t_p=20\mu s, T_j=125^{\circ}C$)		P_{GM}	3	W
Average gate power dissipation($T_j=125^{\circ}C$)		$P_{G(AV)}$	0.2	W

NOTE 1: When we parallel connect a $\leq 1K\Omega$ resistor between Gate and Cathode, the T_j can reach $125^{\circ}C$; if without this resistor, the T_j only can reach $110^{\circ}C$.

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	60	200	μA
V_{GT}		-	-	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.05\text{A}$	-	-	5	mA
dV/dt	$V_D=536\text{V } T_j=125^{\circ}\text{C } R_{GK}=100\Omega$	50	100	-	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=24\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.6	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	10	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	2	mA

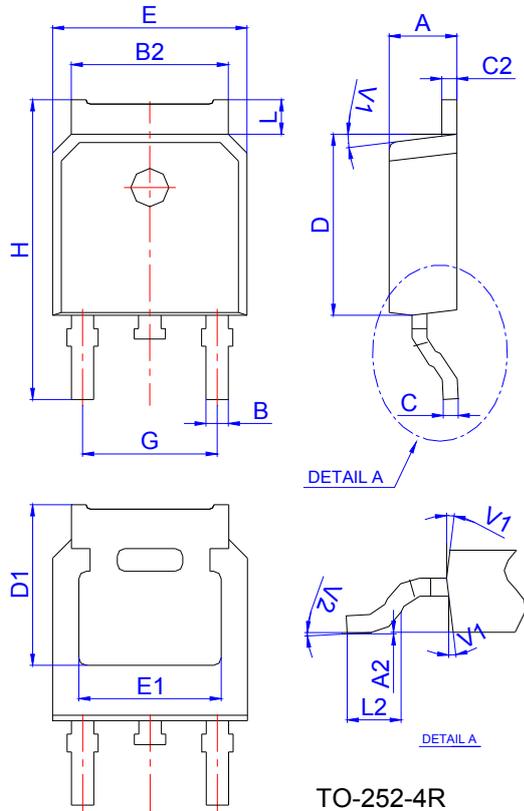
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-252-4R	2.5	$^{\circ}\text{C/W}$
		TO-263	1.7	
$R_{th(j-a)}$	junction to ambient	TO-252-4R	70	$^{\circ}\text{C/W}$
		TO-263	45	

ORDERING INFORMATION

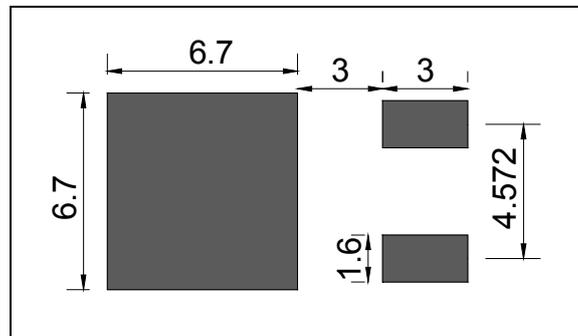
J JieJie Microelectronics Co.,Ltd Sensitive gate SCRs	X $I_{T(RMS)}:12\text{A}$	075	K E:TO-263 K:TO-252-4R ETR:TO-263(Tape&Reel) KTR:TO-252-4R(Tape&Reel)
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PACKAGE MECHANICAL DATA

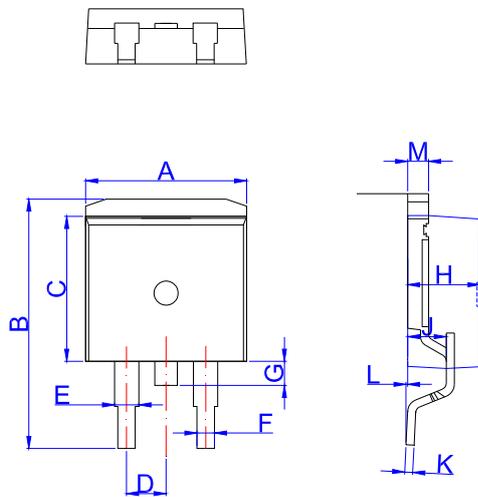


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°		6°

FOOTPRINT-TO-252-4R (dimensions in mm)



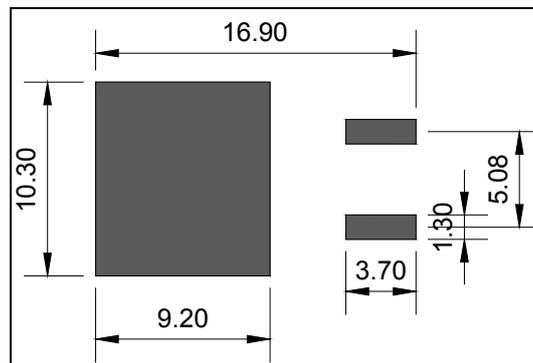
PACKAGE MECHANICAL DATA



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FOOTPRINT-TO-263 (dimensions in mm)



PACKAGE INFORMATION

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-263	TUBE	50	1,000	8,000
TO-252-4R	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-263	TAPING	800	4,000	13 inch
TO-252-4R	TAPING	2,500	25,000	13 inch

MARKING

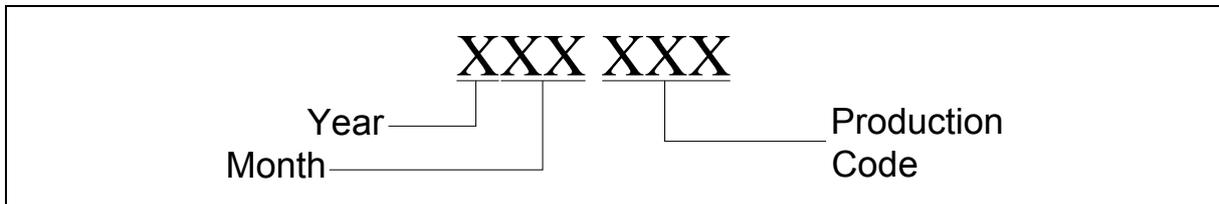
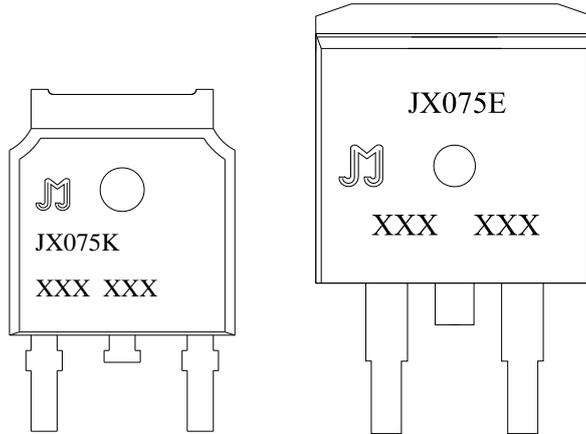


FIG.1 Maximum power dissipation versus RMS on-state current

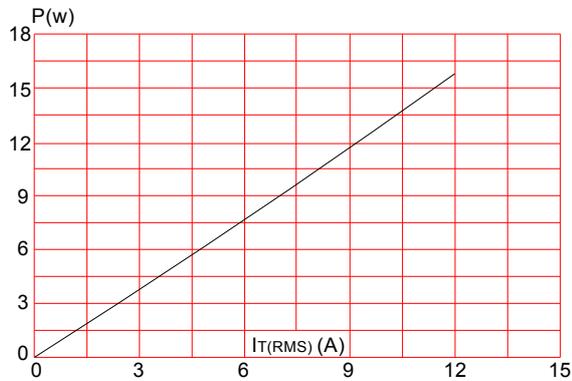


FIG.2 RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35μm)(full cycle)

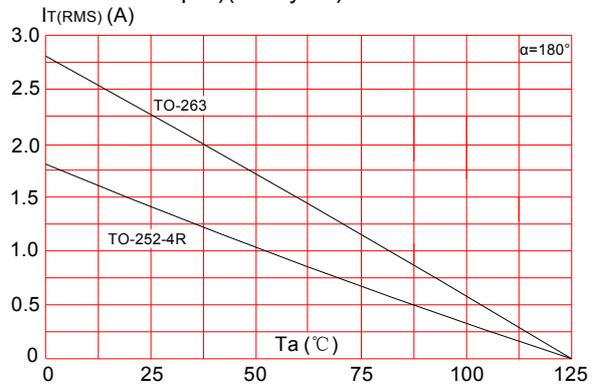


FIG.3 Surge peak on-state current versus number of cycles

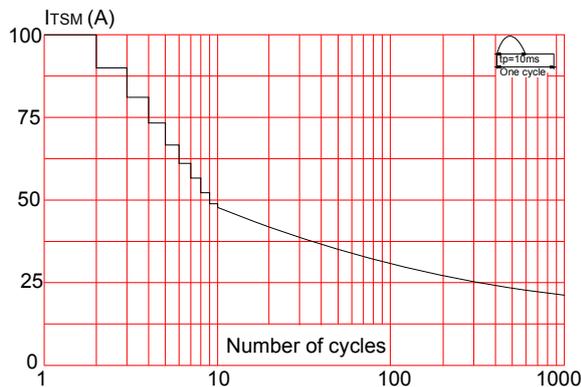


FIG.4 On-state characteristics (maximum values)

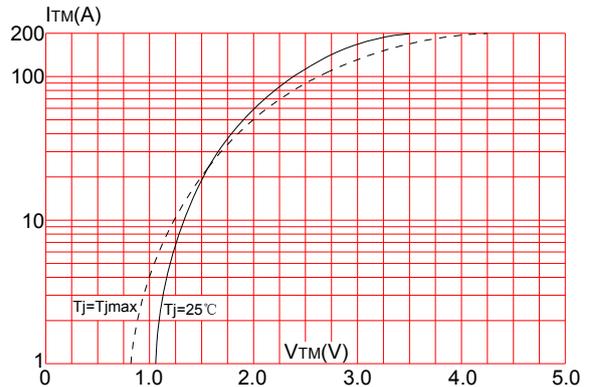


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

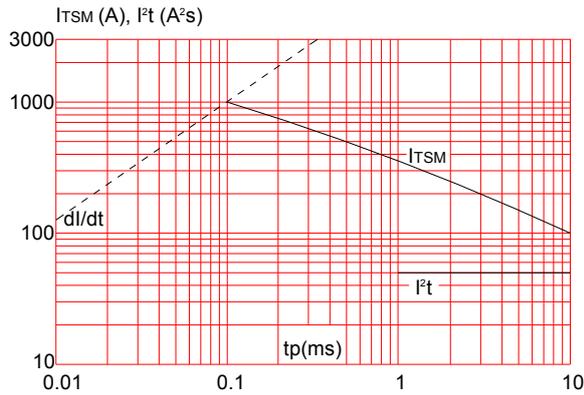
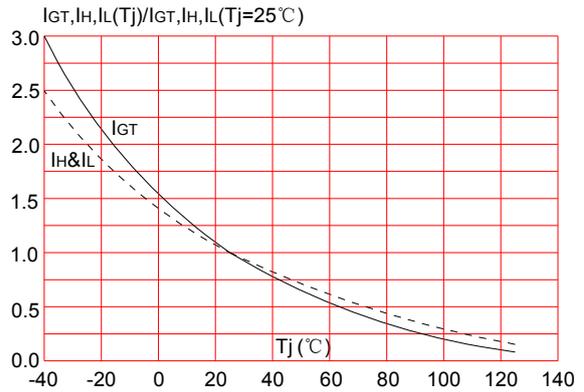
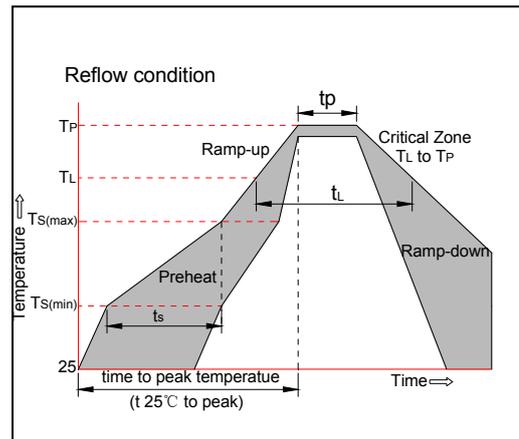


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(\text{min})}$)	+150 $^{\circ}\text{C}$
	-Temperature Max ($T_{s(\text{max})}$)	+200 $^{\circ}\text{C}$
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 $^{\circ}\text{C}/\text{sec}$. Max
$T_{s(\text{max})}$ to T_L - Ramp-up Rate		3 $^{\circ}\text{C}/\text{sec}$. Max
Reflow	-Temperature(T_L) (Liquidus)	+217 $^{\circ}\text{C}$
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) $^{\circ}\text{C}$
Time within 5 $^{\circ}\text{C}$ of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 $^{\circ}\text{C}/\text{sec}$. Max
Time 25 $^{\circ}\text{C}$ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 $^{\circ}\text{C}$



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